



ELECTRONICS, INC.
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NTE2533 Silicon NPN Transistor High-Definition Color Display Horizontal Deflection Output

Features:

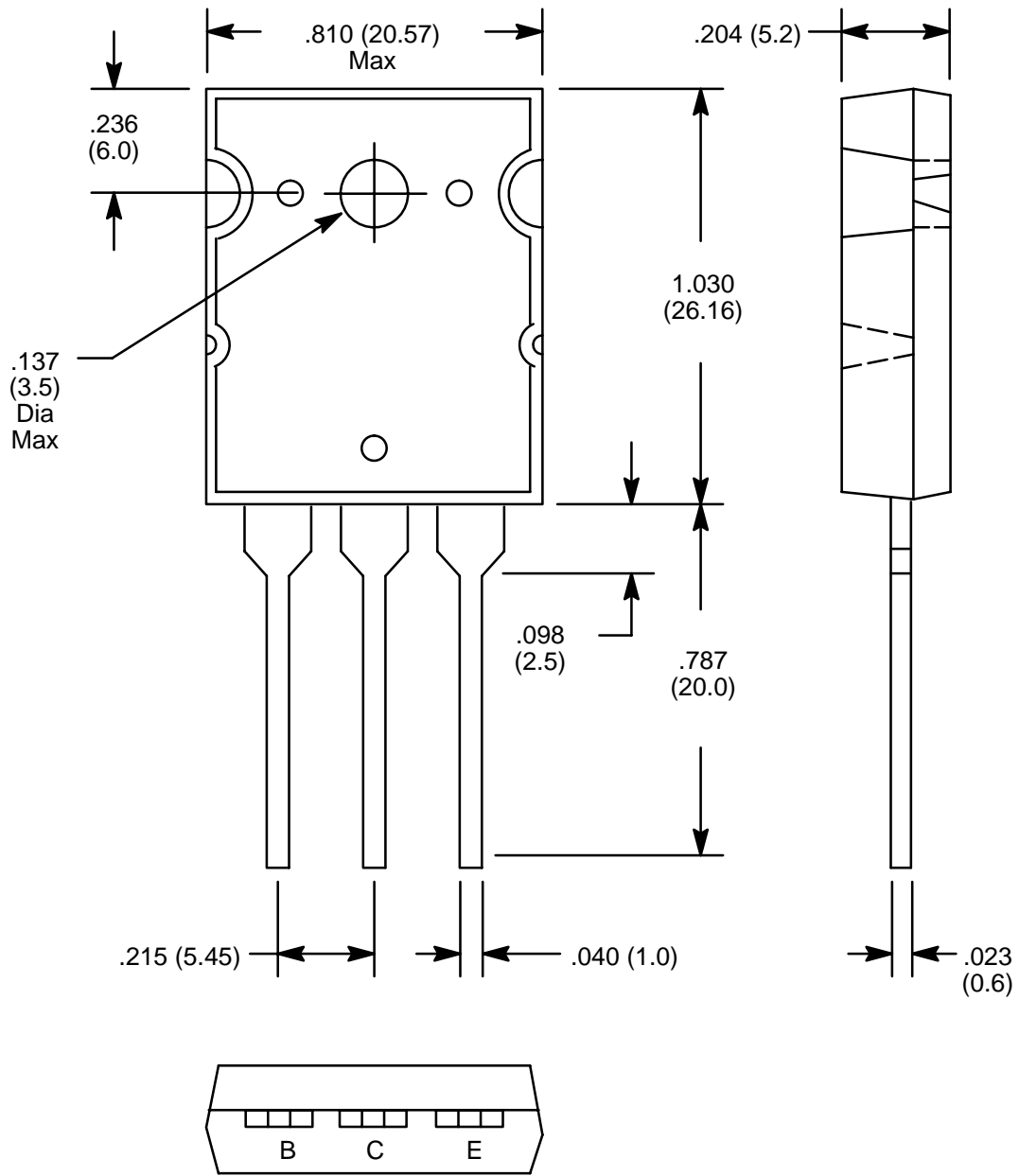
- High Speed: $t_f = 100\text{ns Typ}$
- High Breakdown Voltage: $V_{CBO} = 1500\text{V}$
- High Reliability

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector to Base Voltage, V_{CBO}	1500V
Collector to Emitter Voltage, V_{CEO}	800V
Emitter to Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	25A
Peak	50A
Collector Dissipation, P_C	250W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500\text{V}$	-	-	1.0	mA
	I_{CBO}	$V_{CB} = 800\text{V}, I_E = 0$	-	-	10	μA
Collector Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 100\text{mA}, I_B = 0$	800	-	-	V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$	-	-	1.0	mA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	8	-	30	-
		$V_{CE} = 5\text{V}, I_C = 20\text{A}$	4	-	8	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20\text{A}, I_B = 5\text{A}$	-	-	5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20\text{A}, I_B = 5\text{A}$	-	-	1.5	V
Storage Time	t_{stg}	$I_C = 12\text{A}, I_{B1} = 2.4\text{A},$ $I_{B2} = -4.8\text{A}$	-	-	3	μs
Fall Time	t_f		-	-	0.2	μs



NOTE: Pin2 connected to heatsink